

<b>SANYO</b>	No.4756	2SC4923
	NPN Triple Diffused Planar Silicon Transistor Very High-Definition CRT Display Horizontal Deflection Output Applications	

**Features**

- High speed ( $t_f$  typ. = 100ns).
- High reliability (Adoption of HVP process).
- High breakdown voltage ( $V_{CBO} = 1500V$ ).
- Adoption of MBIT process.

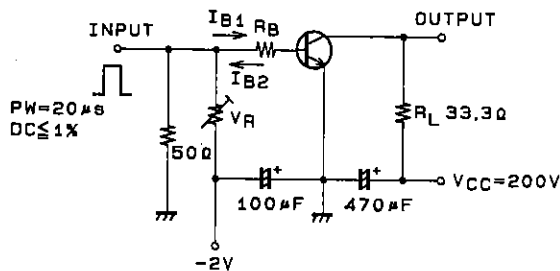
**Absolute Maximum Ratings at  $T_a = 25^\circ C$**

Collector-to-Base Voltage	$V_{CBO}$	1500	V	unit
Collector-to-Emitter Voltage	$V_{CEO}$	800	V	
Emitter-to-Base Voltage	$V_{EBO}$	6	V	
Collector Current	$I_C$	8	A	
Collector Current (Pulse)	$I_{CP}$	25	A	
Collector Dissipation	$P_C$	3.0	W	
		$T_c = 25^\circ C$		
Junction Temperature	$T_j$	70	W	
Storage Temperature	$T_{stg}$	150	$^\circ C$	
		-55 to +150	$^\circ C$	

**Electrical Characteristics at  $T_a = 25^\circ C$**

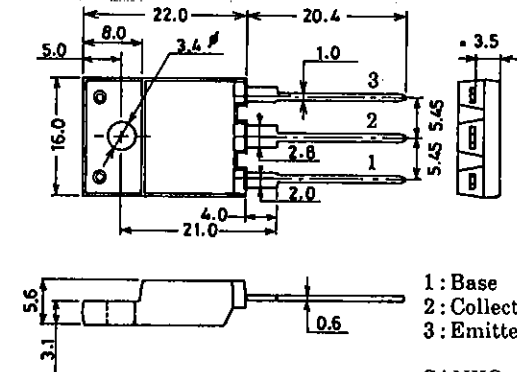
			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 800V, I_E = 0$			10	$\mu A$
	$I_{CES}$	$V_{CE} = 1500V, R_{BE} = 0$			1.0	mA
Collector Sustain Voltage	$V_{CEO(sus)}$	$I_C = 100mA, I_B = 0$	800			V
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 4V, I_C = 0$			1.0	mA
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = 6A, I_B = 1.5A$			5	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = 6A, I_B = 1.5A$			1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5V, I_C = 1A$	8			
	$h_{FE(2)}$	$V_{CE} = 5V, I_C = 6A$	4		8	
Storage Time	$t_{stg}$	$I_C = 6A, I_{B1} = 1.2A, I_{B2} = -2.4A$			3.0	$\mu s$
Fall Time	$t_f$	$I_C = 6A, I_{B1} = 1.2A, I_{B2} = -2.4A$		0.1	0.2	$\mu s$

**Switching Time Test Circuit**



**Package Dimensions 2039C**

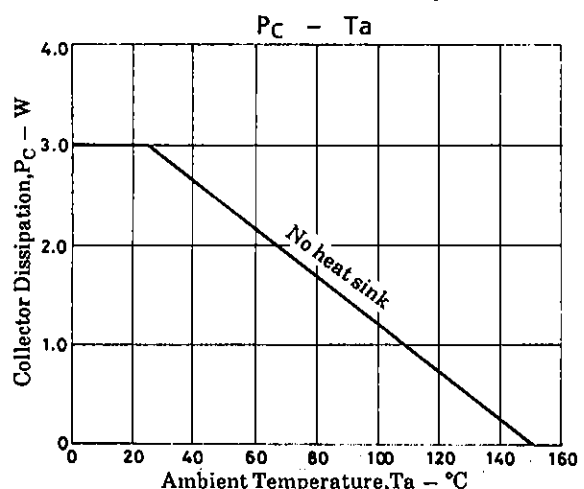
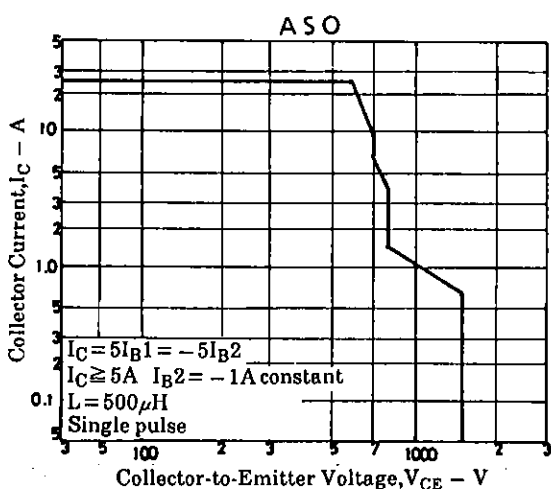
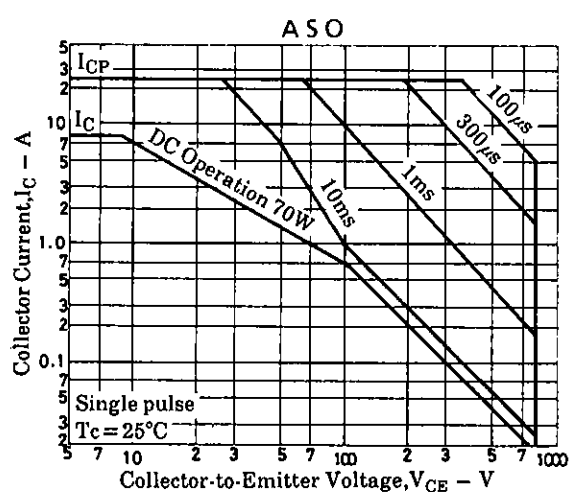
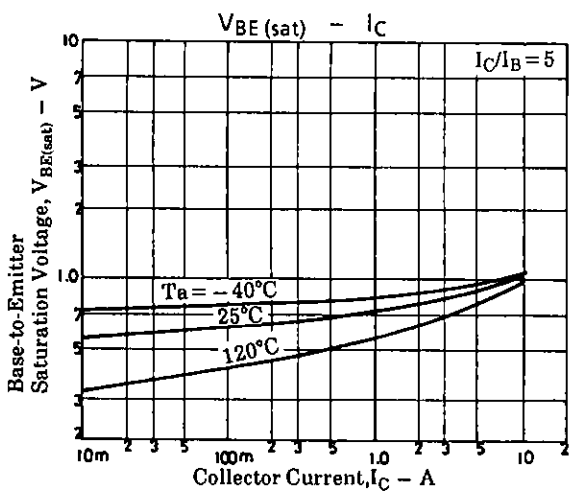
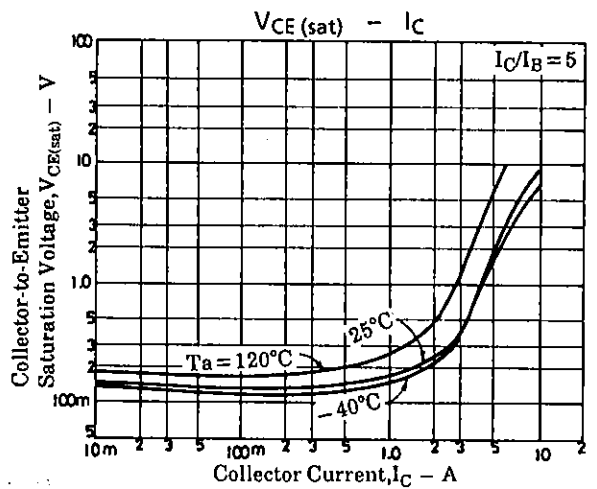
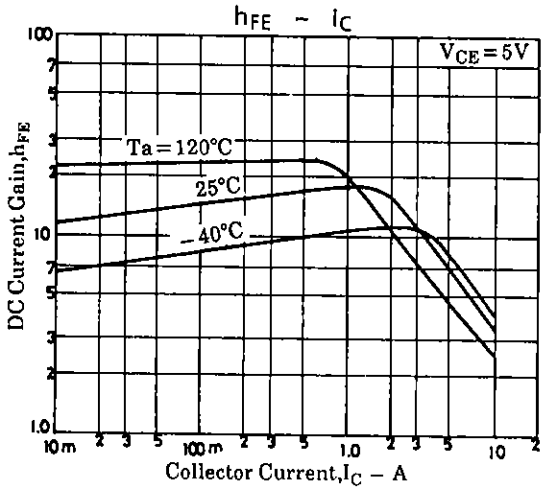
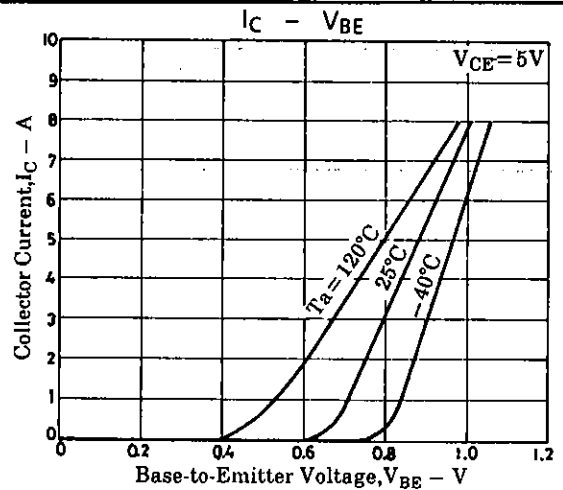
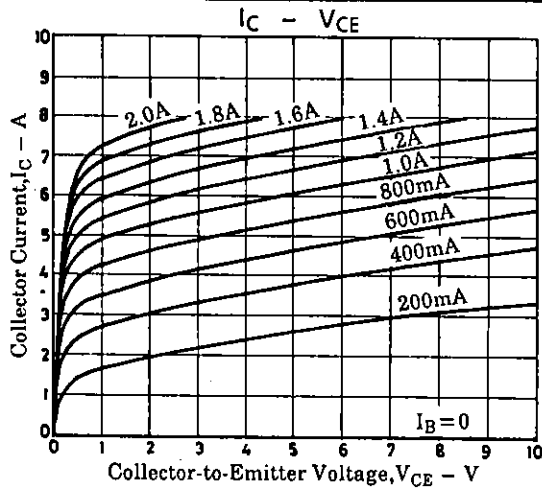
(unit: mm)

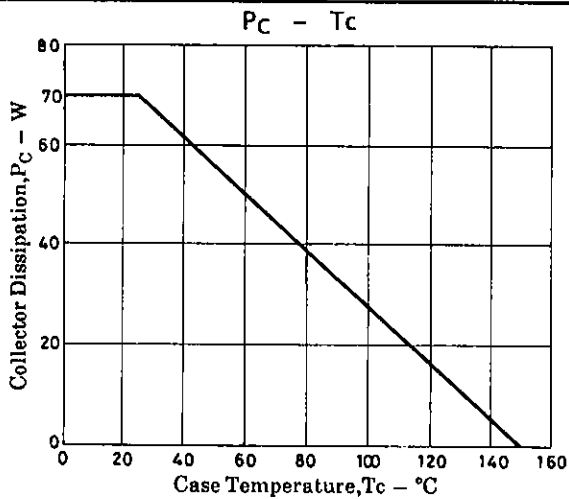


1: Base  
2: Collector  
3: Emitter

SANYO: TO-3PML

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